18 MAR 2004

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
19 April 2001 (19.04.2001)

PCT

(10) International Publication Number
WO 01/27994 A1

(51) International Patent Classification[7]: H01L 21/8247, 27/105

(21) International Application Number: PCT/US00/26874

(22) International Filing Date:
29 September 2000 (29.09.2000)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/417,131 13 October 1999 (13.10.1999) US

(71) Applicant: ADVANCED MICRO DEVICES, INC. [US/US]; One AMD Place, Mail Stop 68, Sunnyvale, CA 94088-3453 (US).

(72) Inventors: HSAIO, Tommy, C.; 707 Continental Cir. #1832, Mountain View, CA 94040 (US). RAMSBEY, Mark, T.; 402 Cumulus Avenue, Sunnyvale, CA 94087 (US). SUN, Yu; 20395 Glasgow Drive, Saratoga, CA 95070 (US).

(74) Agent: RODDY, Richard, J.; Advanced Micro Devices, Inc., One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

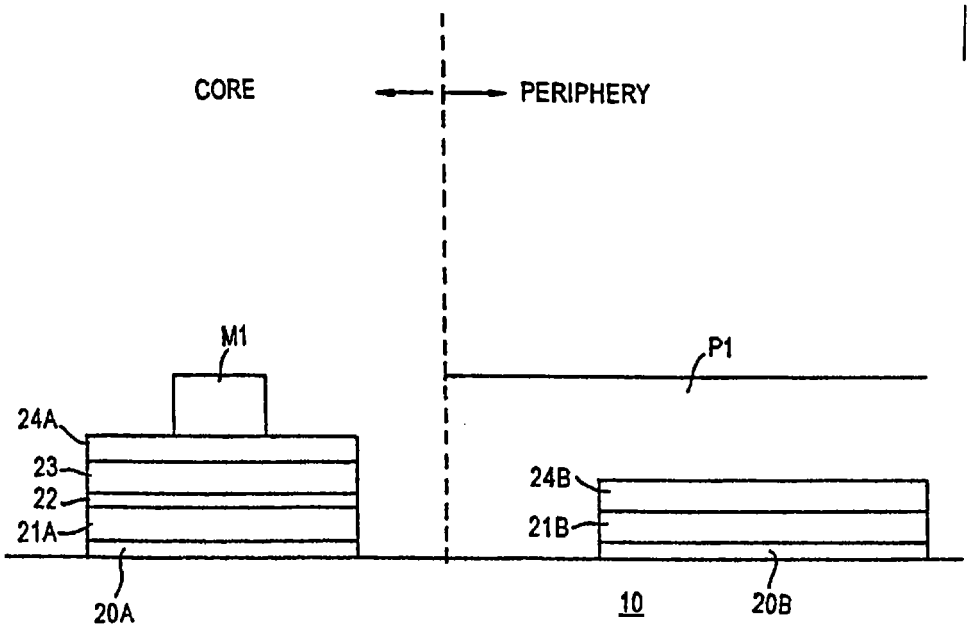
(81) Designated States *(national)*: CN, JP, KR, SG.

(84) Designated States *(regional)*: European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).

Published:
— *With international search report.*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD OF MANUFACTURING A SEMICONDUCTOR MEMORY DEVICE WITH ANTI-REFLECTIVE COATING



162162

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(57) Abstract: Improved dimensional accuracy of the gate electrode structure in the peripheral circuitry region of a semiconductor device is achieved by reducing ARC loss during photoresist stripping associated with plural mask formation in the core memory cell region during patterning and ion implantations. Embodiments include sequentially etching the stacked gate electrode structure in the core memory cell region, photoresist stripping and etching to form the gate electrode structure in the peripheral circuitry region. Subsequently, plural maskings and ion implantations are implemented in the core memory cell region with attendant photoresist strippings.

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